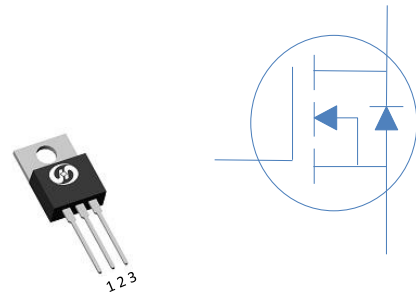


150V N-Ch Power MOSFET

V_{DS}		150	V
$R_{DS(on),typ}$	TO-263	9.4	m
$R_{DS(on),typ}$	TO-220	9.7	m
I_D		91	A



Part Number	Package	Marking
HGB115N15S	TO-263	GB115N15S
HGP115N15S	TO-220	GP115N15S

Absolute Maximum Ratings at $T_J=25^{\circ}\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	$T_C=25^{\circ}\text{C}$	91	A
		$T_C=100^{\circ}\text{C}$	64	
Drain to Source Voltage	V_{DS}	-	150	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	300	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.4\text{mH}, T_C=25^{\circ}\text{C}$	125	mJ
Power Dissipation	P_D	$T_C=25^{\circ}\text{C}$	214	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	$^{\circ}\text{C}$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	R_{JA}	60	$^{\circ}\text{C/W}$
Thermal Resistance Junction-Case	R_{JC}	0.7	$^{\circ}\text{C/W}$

				42	-	
				14	-	nC
				7	-	
Turn on Delay Time	$t_{d(on)}$			17	-	
Rise time	t_r	$V_{DD}=75V, I_D=20A, V_{GS}=10V,$		8	-	ns
Turn off Delay Time	$t_{d(off)}$	$R_G=10 \Omega$		26	-	
Fall Time	t_f			10	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=20A$		0.9	1.2	V
Reverse Recovery Time	t_{rr}					ns
Reverse Recovery Charge	Q_{rr}	$V_R=75V, I_F=20A, di_F/dt=100A/(\mu s)$				

Fig 1. Typical Output Characteristics



Figure 2. On-Resistance vs. Gate-Source Voltage

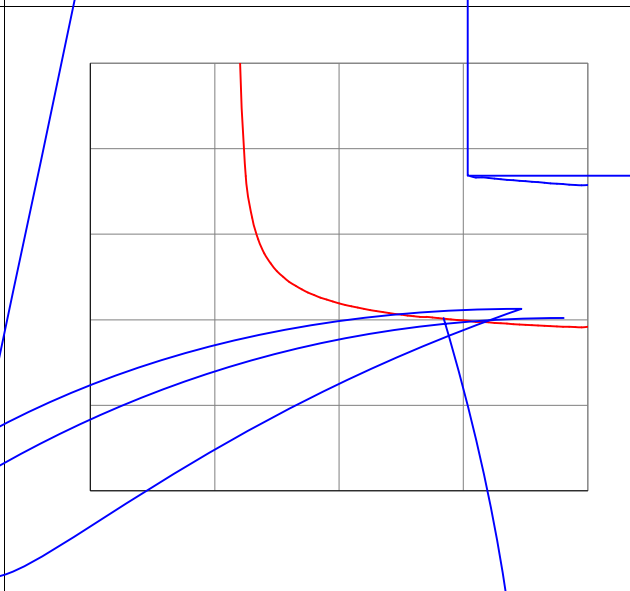


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

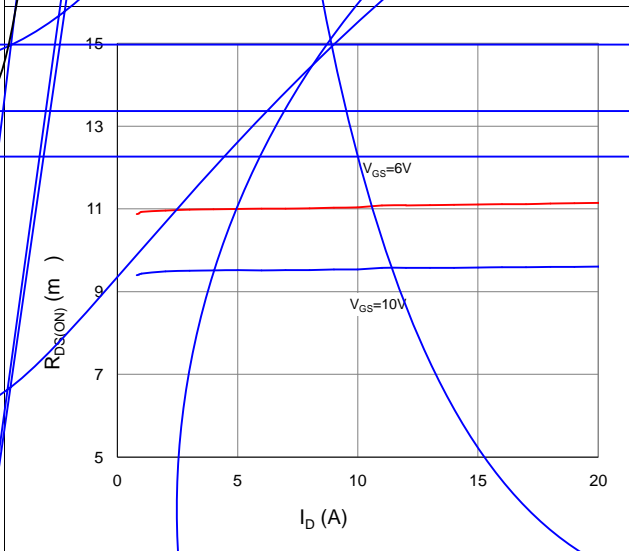


Figure 4. Normalized On-Resistance vs. Junction Temperature

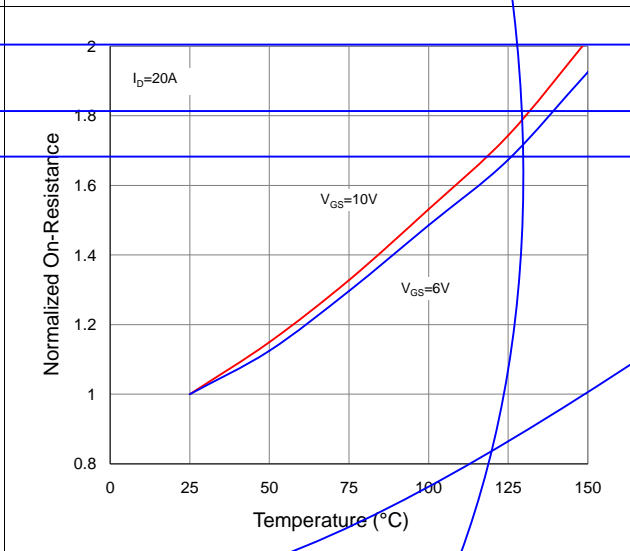


Figure 5. Typical Transfer Characteristics

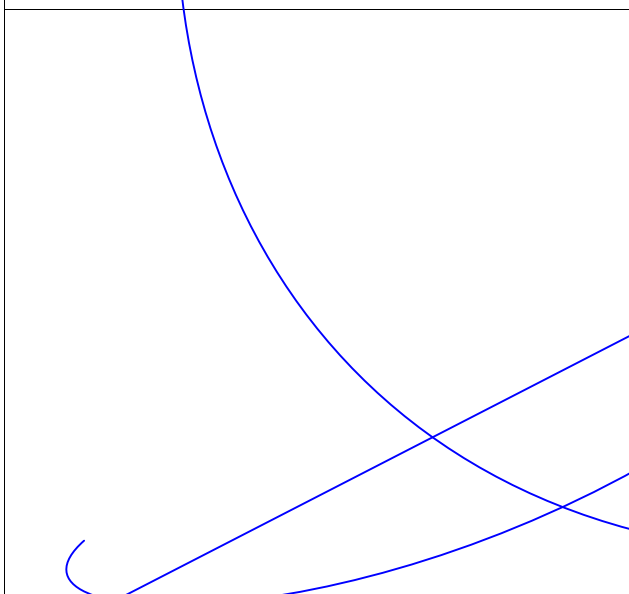


Figure 6. Typical Source-Drain Diode Forward Voltage

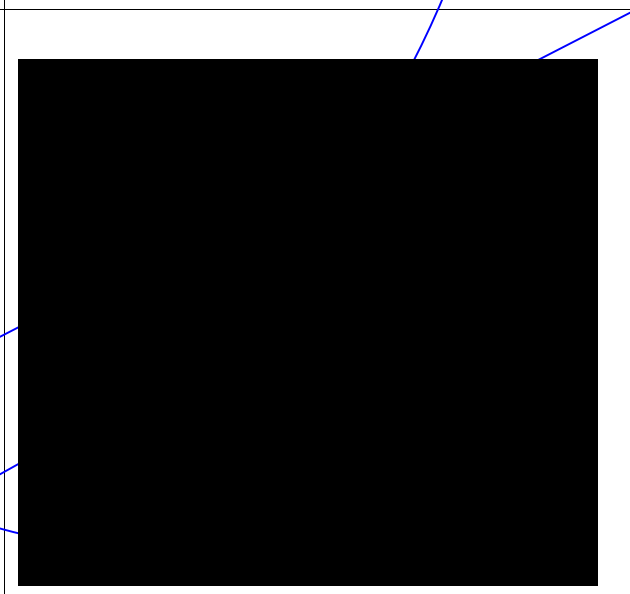


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

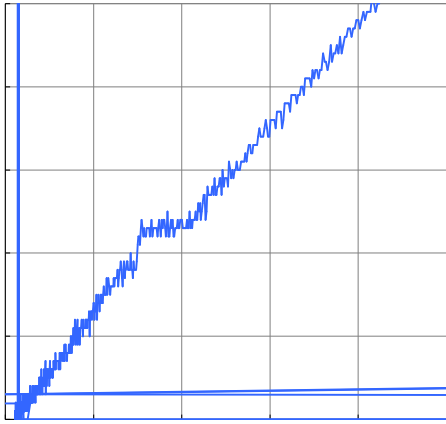


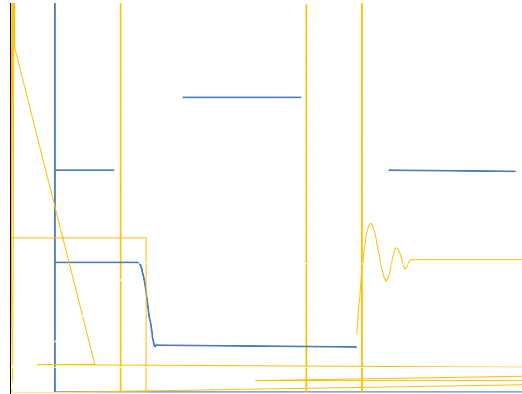
Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

Figure 9. Maximum Safe Operating Area

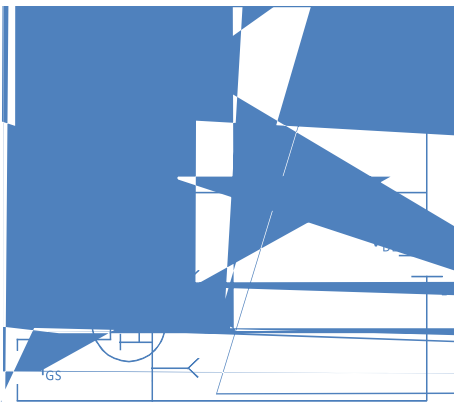
Figure 10. Maximun Drain Current vs. Case Temperature

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

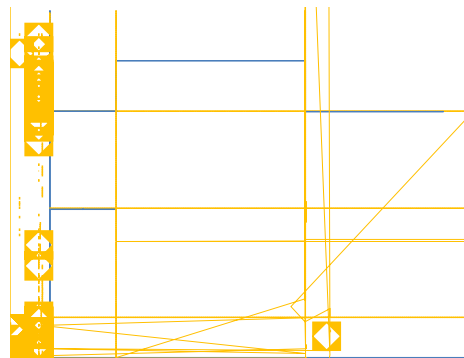
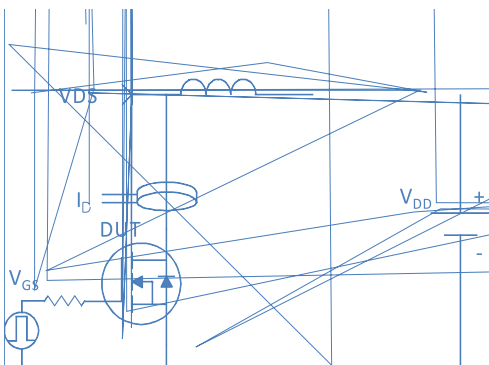
Inductive switching Test



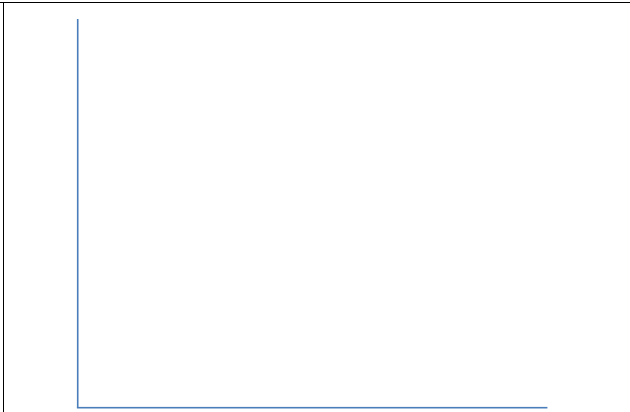
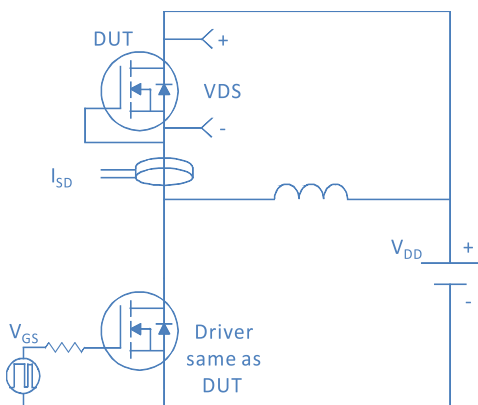
Gate Charge Test



Unclamped Inductive Switching (UIS) Test

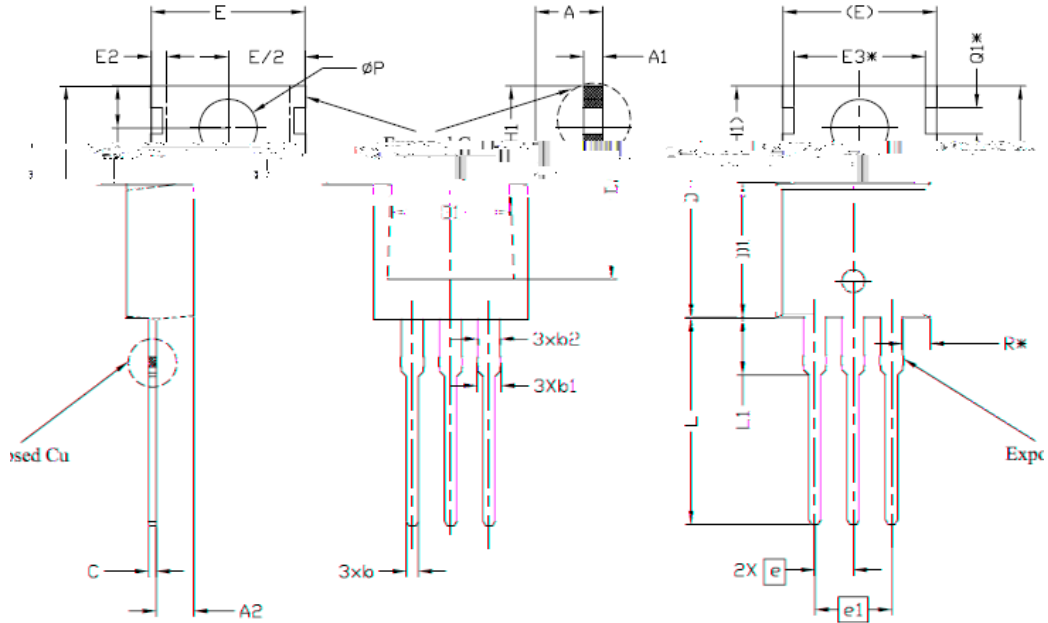


Diode Recovery Test



Package Outline

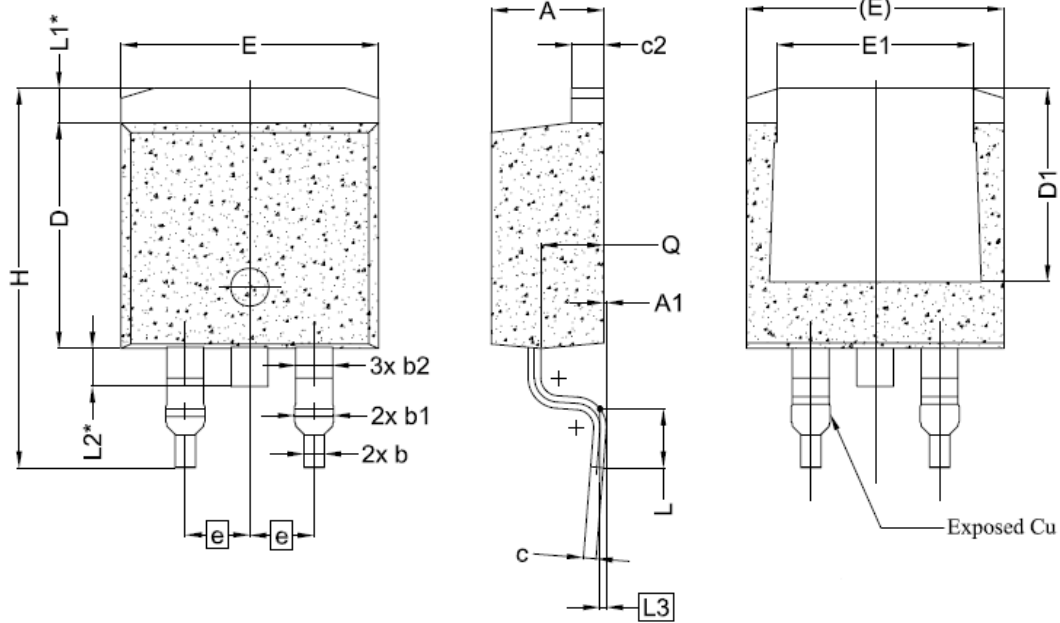
TO-220, 3 leads



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A*	4.13	4.60	4.80	
A2	2.54	2.92	3.10	
B	5.08	5.60	5.90	
B*	1.20	1.55	1.75	
B2	1.20	1.45	1.50	
e	0.76	0.80	0.80	
E	14.70	15.30	16.00	4
E*	3.30	3.80	4.00	
E2	12.50	12.70	12.85	4
E3*	3.68	4.12	4.38	4,5
E4	6.06	7.25	8.00	4
E5			8.16	4
L3*		0.76(3)		
e		2.54(10)		
e1		5.08(20)		
H*	6.30	6.45	6.50	5,3
I	13.47	13.72	13.97	
L1	3.80	3.80	4.00	
ØP	3.75	3.84	3.95	
Q	2.80	2.80	3.00	
Q1*		1.78(REF)		
R*		1.62(REF)		

Package Outline

TO-263, 3 leads



Symbol	Dimension	Value	Symbol	Dimension	Value
A	Lead length	4.24	A1	Lead diameter	0.95
b	Lead width	0.95	b1	Lead width	0.95
b1	Lead width	0.95	b2	Lead width	0.95
b2	Lead width	0.95	c	Lead diameter	0.95
c	Lead diameter	0.95	c2	Lead thickness	0.15
c2	Lead thickness	0.15	D	Package diameter	9.02
D	Package diameter	9.02	D1	Package diameter	9.02
D1	Package diameter	9.02	D2	Package diameter	9.02
D2	Package diameter	9.02	E	Package width	7.25
E	Package width	7.25	E1	Package width	7.25
E1	Package width	7.25	E2	Package width	7.25
E2	Package width	7.25	H	Package height	15.88
H	Package height	15.88	L1	Lead length	2.79
L1	Lead length	2.79	L2	Lead length	1.36
L2	Lead length	1.36	L3	Lead length	1.50
L3	Lead length	1.50	Q	Lead diameter	0.25
Q	Lead diameter	0.25			